

isc N-Channel MOSFET Transistor
IXFP130N10T
• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 9.1\text{m}\Omega @ V_{GS}=10\text{V}$
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATION

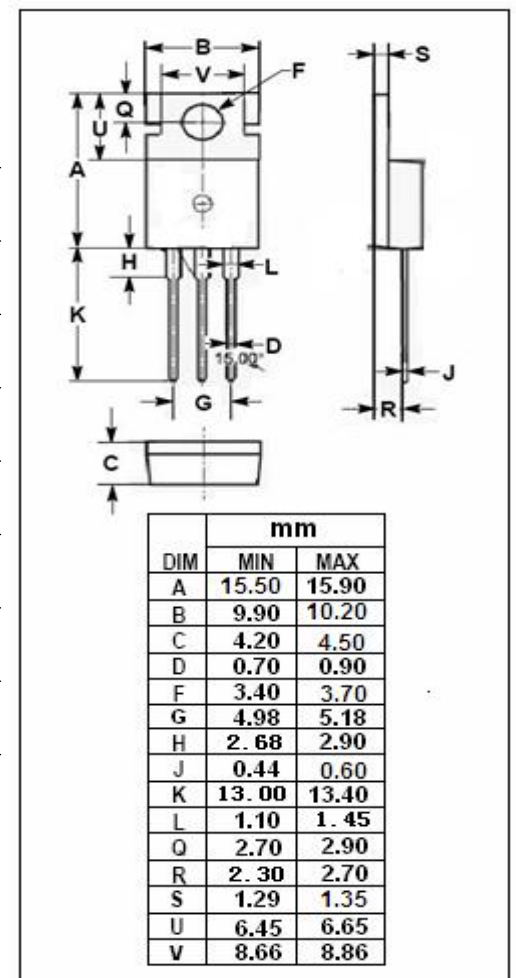
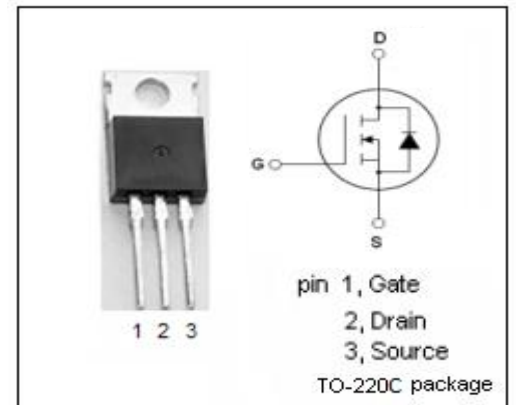
- DC/DC Converters
- High Current Switching Applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	130	A
I_{DM}	Drain Current-Single Pulsed	350	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	360	W
T_j	Operating Junction Temperature	-55~175	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~175	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Junction-to-case thermal resistance	0.42	$^\circ\text{C}/\text{W}$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V; I _D = 250 μ A	100		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.5	4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 25A		9.1	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} =0V		±200	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		10	μ A
		V _{DS} = V _{DSS} ; V _{GS} = 0V; T _J = 150°C		500	
V _{SD}	Diode forward voltage	I _F = 25A; V _{GS} = 0V		1.0	V

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